



TO-92 Plastic-Encapsulate Transistors

2N5172 TRANSISTOR (NPN)

FEATURES

Power dissipation

$$P_{CM} : 0.625 \text{ W (Tamb=25}^{\circ}\text{C)}$$

Collector current

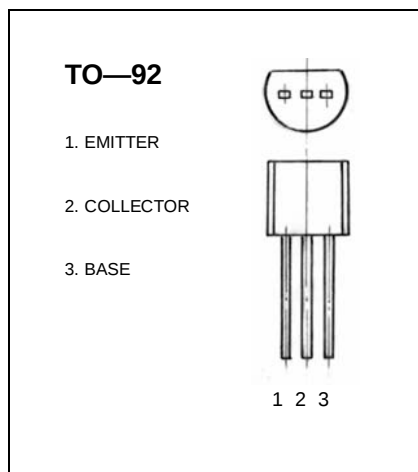
$$I_{CM} : 0.5 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : 25 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}\text{C to } +150^{\circ}\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10 \text{ mA}, I_B = 0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 25V, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5 \text{ V}, I_C = 0$			0.1	μA
DC current gain	h_{FE}	$V_{CE} = 10V, I_C = 10mA$	100		500	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 1mA$			0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 10mA, I_B = 1mA$			1.2	V